

PRELIMINARY

SPECIFICATION OF LED CHIP

CE640-200

[RED]

1) Commodity Type and Physical Characteristics.

1. Material	AlGaInP/GaAs	
2. Electrode	Top Side P (anode) side	: Au Alloy
	Bottom Side N (cathode) side	: Au Alloy
3. Electrode Pattern		Fig.1
4. Chip Size	510um*320um	Fig.1
5. Chip Thickness	260um	Fig.1
6. Emission Area	φ 200um	Fig.1

2) Electro-Optical Characteristics

Parameters	Symbol	Condition	min.	typ.	max.	unit
Forward Voltage	V _f	I _f =20mA		1.90	2.20	V
Reverse Current	I _r	V _r =5V			10	uA
Radiant Power	P _o	I _f =20mA	0.6	0.8	1.2	mW
Luminous Intensity	I _v	I _f =20mA	50	70		mcd
Side Emission	-	I _f =20mA			0	%
Peak Wavelength	λ _p	I _f =20mA	630	640	650	nm
Spectral Radiation Bandwidth	Δλ	I _f =20mA		13		nm
RiseTime	t _r	I _f =20mA		150		ns
FallTime	t _f	I _f =20mA		150		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.(Ta=25°C)

[Unit: um]

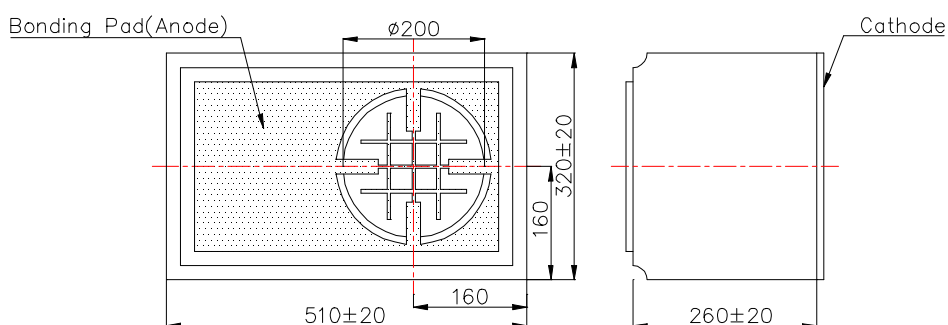


Fig.1 Electrode Pattern, Chip size and Emission Area